

MDL-III-808/1~2500mW

INFRARED DIODE LASER AT 808nm

Diode infrared laser module at 808nm is made features of ultra compact, long lifetime, low cost and easy operating, which is used in measurement, communication, spectrum analysis, etc.



SPECIFICATIONS

Wavelength (nm)	808±3		
Output power (mW)	>1, 100, 200, 300, ..., 2500		
Transverse mode	Near TE ₀₀		
Operating mode	CW		
Power stability (rms, over 4 hours)	<1%, <3%, <5%		
Warm-up time (minutes)	<5		
M ² factor	<20		
Beam divergence, full angle (mrad)	<3.0		
Dimensions of beam at the aperture (mm)	~5×8		
Beam height from base plate (mm)	24.8		
Polarization ratio	>50:1		
Pointing stability after warm-up (mrad)	<0.05		
Operating temperature (°C)	10~35		
Power supply (90-264VAC or 5VDC)	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
TTL / Analog modulation	Optional, 2kHz or higher (on request, up to 30kHz)		
Expected lifetime (hours)	10000		
Warranty	1 year		



MxL-III-808	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
<p>140.8(L)×73(W)×46.2(H) mm³, 0.6kg</p>	<p>154 (L) ×155(W) ×95 (H) mm³, 1.5kg</p>	<p>133 (L) ×130(W) ×65 (H) mm³, 1.2kg</p>	<p>100 (L) ×60(W) ×56 (H) mm³, 0.2kg</p>